		1449 (Modified)	ICATIONS	ATTY. DOCKET NO. YOR920000344US1			RIAL NO. 692606 (	-			
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT					APPLICANT: Chu et al.						
JAN 0 4 2002 E					FILING DATE: G Oct. 19, 2000			ROUP:			
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.